

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Walter David BRADDOCK

INT APP. NO: 09/636,484

FILED: 8/10/2000

FOR: Integrated Transistor Devices

GAU: 2811

EXAMINER: Donghee KANG

PTO Confirmation. No. 6691



37 CFR 1.97 INFORMATION DISCLOSURE STATEMENT

ASSISTANT COMMISSIONER FOR PATENTS  
ALEXANDRIA, VA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- ☒ The applicant(s) wish to make of record the references listed on the attached PTO-1449. Copies of the listed references are being submitted herewith or, were submitted in the parent or grandparent application, where required, as were either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references, or cited by the examiner.
- ☐ A check is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- ☐ Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s) is attached along with PTO 1449.
- ☐ A check is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

- ☐ Each item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

PETITION

- ☐ Applicant(s) hereby request consideration of the attached information. A check is attached in the amount of the Petition fee required under 37 CFR §1.17(p).

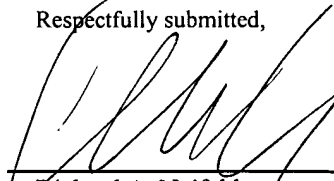
DEPOSIT ACCOUNT

- ☒ Please charge any additional fees for the papers being filed herewith and for which no check is enclosed herewith, or credit any overpayment to deposit account number 50-2106. A duplicate copy of this sheet is enclosed.

31518

PATENT TRADEMARK OFFICE

Respectfully submitted,

  
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12/22/04

Date

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NEIFELD IP LAW REFERENCE FOR PATENT & TRADEMARK LIST OF REFERENCES CITED BY THE APPLICANT (Rev: 5/14/2003)	NEIFELD REF: OSEM-DB3	APPLICATION NO: 09/636,484
	FIRST NAMED INVENTOR: BRADDOCK	
	FILING DATE: 8/10/2000	GROUP ART UNIT: 2811

## LISTING OF UNITED STATES PATENTS

EXAMINER INITIALS	REFERENCE NUMBER (U SERIES)	PATENT NUMBER	ISSUE DATE	NAME OF PATENTEE OR APPLICANT	PAGE/LINE AND FIGURE/ELEMENT OF RELEVANT MATERIAL AND/OR IDENTIFICATION OF PRIORITY APPLICATION IN WHICH REFERENCE IS CITED
	U-1	3,950,273	4-1976	Jones	Already of Record
	U-2	4,404,265	9-1983	Manascvit	Already of Record
	U-3	4,410,902	10-1983	Matik	Already of Record
	U-4	4,416,952	11-1983	Nishizawa et al.	Already of Record
	U-5	4,561,915	12-1985	Mito	Already of Record
	U-6	4,624,901	11-1986	Glass	Already of Record
	U-7	4,671,777	6-1987	van Esdonk et al.	Already of Record
	U-8	4,685,193	8-1987	Faria et al.	Already of Record
	U-9	4,745,082	5-1988	Kwok	Already of Record
	U-10	4,802,180	1-1989	Brandt, Jr. et al.	Already of Record
	U-11	4,843,450	6-1989	Kirchner et al.	Already of Record
	U-12	4,859,253	8-1989	Duchanan et al.	Already of Record
	U-13	4,935,789	6-1990	Calvillo	Already of Record
	U-14	4,970,060	11-1990	Belt et al.	Already of Record
	U-15	5,055,445	10-1991	Belt et al.	Already of Record
	U-16	5,124,762	6-1992	Childs et al.	Already of Record
	U-17	5,170,407	12-1992	Schubert et al.	Already of Record
	U-18	5,270,798	12-1993	Pao et al.	Already of Record
	U-19	5,323,053	6-1994	Luryi et al.	Already of Record
	U-20	5,386,137	1-1995	Dell et al.	Already of Record
	U-21	5,425,043	6-1995	Holonyak et al.	Already of Record
	U-22	5,451,548	9-1995	Hunt et al.	Already of Record
	U-23	5,491,712	2-1996	Lin et al.	Already of Record
	U-24	5,550,089	8-1996	Dutta et al.	Already of Record
Date:			Examiner's Signature:		

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	U-25	5,597,768	1-1997	Passlack et al.	Already of Record
	U-26	5,640,751	6-1997	Faria	Already of Record
	U-27	5,665,658	9-1997	Passlack	Already of Record
	U-28	5,693,565	12-1997	Camilletti et al.	Already of Record
	U-29	5,729,563	3-1998	Wang et al.	Already of Record
	U-30	5,767,388	6-1998	Fleisher et al.	Already of Record
	U-31	5,805,624	9-1998	Yang et al.	Already of Record
	U-32	5,821,171	10-1998	Hong et al.	Already of Record
	U-33	5,838,708	11-1998	Lin et al.	Already of Record
	U-34	5,896,408	4-1999	Corzine et al.	Already of Record
	U-35	5,930,611	7-1999	Okamoto	Already of Record
	U-36	5,945,718	8-1999	Passlack et al.	Already of Record
	U-37	5,953,362	9-1999	Pamulapati et al.	Already of Record
	U-38	6,006,582	12-1999	Bhandari et al.	Already of Record
	U-39	6,028,693	2-2000	Fork et al.	Already of Record
	U-40	6,030,453	2-2000	Passlack et al.	Already of Record
	U-41	6,045,611	4-2000	Ishii et al.	Already of Record
	U-42	6,069,908	5-2000	Yuen et al.	Already of Record
	U-43	6,071,780	6-2000	Okamoto et al.	Already of Record
	U-44	6,094,295	7-2000	Passlack et al.	Already of Record
	U-45	6,114,079	9-2000	Christian et al.	Already of Record
	U-46	6,150,677	11-2000	Tanaka et al.	Already of Record
	U-47	6,207,976	3-2001	Takahashi et al.	Already of Record
	U-48	6,252,896	6-2001	Tan et al.	Already of Record
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### LISTING OF NON PATENT LITERATURE

EXAMINER INITIALS	REFERENCE NUMBER (L Series)	PUBLICATION DATE	INCLUDE IN SEQUENCE: Name of first author (in CAPITAL LETTERS), Title in quotation marks, name of publication, date of publication, page numbers, publisher, city of publication, and country of publication	ENGLISH LANGUAGE TRANSLATION ATTACHED? (YES OR NO) AND/OR OR IDENTIFICATION OF PRIORITY APPLICATION IN WHICH REFERENCE IS CITED
	L-1	1994	"1995-1996 Alfa AESAR Catalog," 1994, page 1244, Johnson-Matthey Catalog Company, Inc., Ward Hill, MA, US.	Already of Record
	L-2	6-2001	VURGATMAN et al., "Band Parameters for III-V Semiconductors and Their Alloys," J. Appl. Phys. PP 5816-5875 (June 1, 2001).	Already of Record
	L-3	2003	"Gallium Oxide on Gallium Arsenide: Atomic Structure, Materials, and Devices," Chapter 12, either published or scheduled for publication in "Gallium Oxide on Gallium Arsenide: Atomic Structure, Materials, and Devices," in III-IV Semiconductor Heterostructures: Physics and Devices, edited by W.Z. Cai, Transworld Research Publisher, Kerala, India (2003).	Already of Record
	L-4	7-1996	PASSLACK et al., "Thermodynamic and photochemical stability of low interface state density Ga <sub>2</sub> O <sub>3</sub> -GaAs structures fabricated by in-situ molecular beam epitaxy", Applied Physics Letters, Vol 69, No 3, pps 302-304, 15 July 1996.	Already of Record
	L-5	6-1997	PASSLACK et al., "Recombination velocity at oxide-GaAs interfaces fabricated by in-situ molecular beam epitaxy", Applied Physics Letters, Volume 68, Number 25, pages 3605-3607, 17 June 1997.	Already of Record
	L-6	2-1996	PASSLACK et al., "Quasistatic and high frequency capacitance-voltage characterization of Ga <sub>2</sub> O <sub>3</sub> -GaAs structures fabricated by in-situ molecular beam epitaxy", Applied Physics Letters, Volume 68, Number 8, pages 1099-1101, 19 February 1996.	Already of Record
	L-7	8-1997	UEDA et al., "Anisotropy of electrical and optical properties in B-Ga <sub>2</sub> O <sub>3</sub> single crystals", Applied Physics Letters, Volume 71, Number 7, Pages 933-935, 18 August 1997.	Already of Record

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	E-8	6-1997	UEDA et al., "Synthesis and control of conductivity of ultraviolet transmitting B-Ga <sub>2</sub> O <sub>3</sub> single crystals", Applied Physics Letters, Volume 70, Number 26, pages 3561-3563, 30 June 1997.	Already of Record
	E-9	2-2000	KHAN et al., "AlGa <sub>N</sub> /Ga <sub>N</sub> Metal Oxide Semiconductor Heterostructure Field Effect Transistor", IEEE Electron Device Letters, Volume 21, Number 2, pages 63-65, Feb. 2000.	Already of Record
	E-10	3-2004	Takebe et al., "GaAs MISFETs With Insulating Gate Films Formed by Direct Oxidation and by Oxinitridation for Recessed GaAs Surfaces	Already of Record
	Θ-1	4/28/1965	BECKE et al., "Gallium Arsenide MOS Transistors," Solid-State Electronics, 1965, Vol. 8, pp. 813-822, Great Britain.	Already of Record
	Θ-2	12/3/1995	PASSLACK et al., "C-V and G-V Characterization of In-Situ Fabricated Ga <sub>2</sub> O <sub>3</sub> -GaAs Interfaces for Inversion/Accumulation Device and Surface Passivation Applications," Solid-State Electronics, 1996, Vol. 39, No. 8, pp. 1133-1136, Great Britain.	Already of Record
	Θ-3	2/19/1996	PASSLACK et al., "Quasistatic and high frequency capacitance-voltage characterization of Ga <sub>2</sub> O <sub>3</sub> -GaAs structures fabricated by in-situ molecular beam epitaxy", Applied Physics Letters, Volume 68, Number 8, pages 1099-1101, 19 February 1996.	Already of Record
	Θ-4	1996	PASSLACK et al., "GaAs Surface Passivation Using inSitu Oxide Deposition," Applied Surface Science, 1996, pp. 441-447.	Already of Record
	Θ-5	6/1995	PASSLACK et al., "Infrared Microscopy Studies on High-Power InGaAs-GaAs-InGaP Lasers with Ga <sub>2</sub> O <sub>3</sub> Facet Coatings," IEEE Journal of Selected Topics in Quantum Electronics, Vol. 1, No. 2, June 1995, pp. 110-115.	Already of Record
	Θ-6	12/15/1995	PASSLACK et al., "Capacitance-Voltage and Current-Voltage Characterization of Al <sub>x</sub> Ga <sub>1-x</sub> As-GaAs Structures," J. Appl. Phys., Vol. 78, No. 12, December 15, 1995, pp. 7091-7098.	Already of Record
	Θ-7	1997	HONG et al., "Novel Ga <sub>2</sub> O <sub>3</sub> (Gd <sub>2</sub> O <sub>3</sub> ) Passivation Techniques to Produce Low-Dit Oxide-GaAs Interfaces," Journal of Crystal Growth, 1997, pp. 422-427.	Already of Record
	Θ-8	5/1/1996	HONG et al., "Low Interface State Density Oxide-GaAs Structures Fabricated by in-Situ Molecular Beam Epitaxy," J. Vac. Sci. Technol. B., Vol. 14, No. 3, May/Jun 1996, pp. 2297-2300.	Already of Record



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	0-9	2/1/1997	PASSLACK et al., "Low Dit, Thermodynamically Stable Ga <sub>2</sub> O <sub>3</sub> -GaAs Interfaces: Fabrication, Characterization, and Modeling," IEEE Transactions on Electron Devices, Vol. 44, No. 2, February 1997, pp. 214-225.	Already of Record
Date:			Examiner's Signature:	

**BTM**

**Printed: December 16, 2004 (4:44pm)**

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